

ABSTRACT AMENDMENTS

Replace the Abstract with:

~~The present invention provides an~~ An underlayer film-forming material for copper, a method for forming the underlayer, an underlayer film for copper, and a semiconductor device including a substrate, the underlayer and copper wiring film, which ~~enable the prevention of~~ prevents copper diffusion as well as ~~provide~~ provides superior adhesion to a copper wiring film, even if the film is thinner than conventional barrier metals. The underlayer film-forming material for copper ~~includes~~ is formed from a compound represented by a ~~following general formula [I]:~~ $(R_1R_2)P-(R)_n-Si(X_1X_2X_3)$, wherein at least one of X_1 , X_2 , and X_3 represents a hydrolysable group; each of R_1 and R_2 represents an alkyl group; R represents a divalent linear organic group which is ~~formed of~~ selected from an alkylene group, an aromatic ring, ~~or~~ and an alkylene group including an aromatic ring; and n ~~represents~~ is an integer ~~of~~ from 1 to 6.